

ES2AF THRU ES2JF-HAF

Surface Mount Superfast Recovery Rectifier

Reverse Voltage - 50 to 600 V

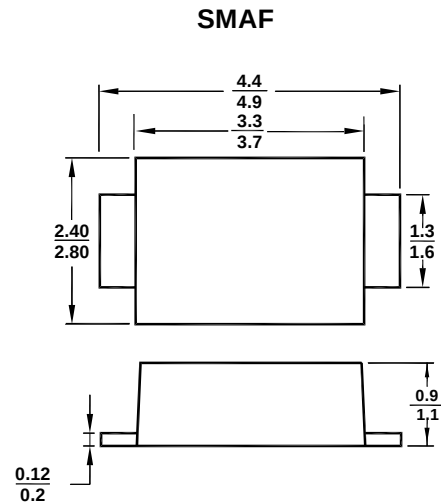
Forward Current - 2 A

Features

- Glass Passivated Chip Junction
- For surface mounted applications
- Low profile package
- Superfast reverse recovery time
- Halogen and Antimony Free(HAF), RoHS compliant

Mechanical Data

- **Case:** SMAF
- **Terminals:** Solder plated, solderable per MIL-STD-750, Method 2026



All Dimensions in mm

Absolute Maximum Ratings and Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20%.

Parameter	Symbols	ES2AF	ES2BF	ES2CF	ES2DF	ES2EF	ES2GF	ES2JF	Units
	Marking	ES2A	ES2B	ES2C	ES2D	ES2E	ES2G	ES2J	-
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	150	200	300	400	600	V
Maximum RMS Voltage	V _{RMS}	35	70	105	140	210	280	420	V
Maximum DC Blocking Voltage	V _{DC}	50	100	150	200	300	400	600	V
Maximum Average Forward Rectified Current at T _L =100°C	I _{F(AV)}	2							A
Peak Forward Surge Current 8.3 ms Single Half Sine Wave Superimposed on Rated Load (JEDEC Method)	I _{FSM}	50							A
Maximum Forward Voltage at 2 A	V _F	1				1.25		1.7	V
Maximum Reverse Current T _a = 25°C at Rated DC Blocking Voltage T _a = 125°C	I _R	5 100							μA
Typical Junction Capacitance at V _R = 4 V, f = 1 MHZ	C _j	60							pF
Maximum Reverse Recovery Time at I _F = 0.5 A, I _R = 1 A, t _{rr} = 0.25 A	t _{rr}	35							ns
Typical Thermal Resistance	R _{θJA}	75							°C/W
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to + 150							°C

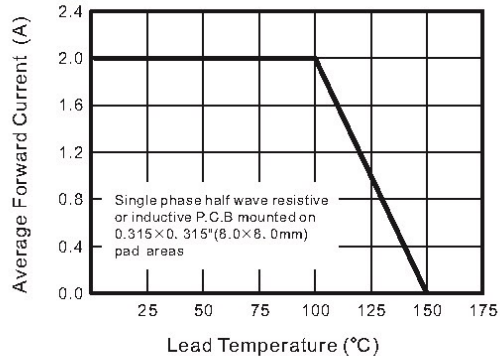
TOP DYNAMIC



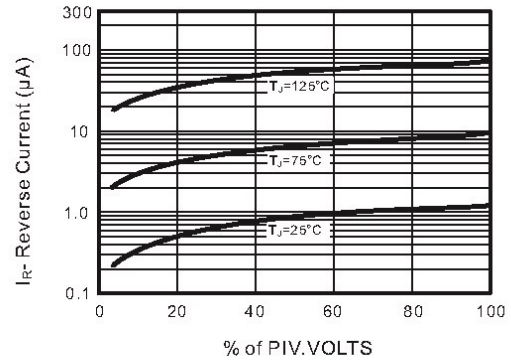
Dated: 25/08/2016 JD Rev: 03

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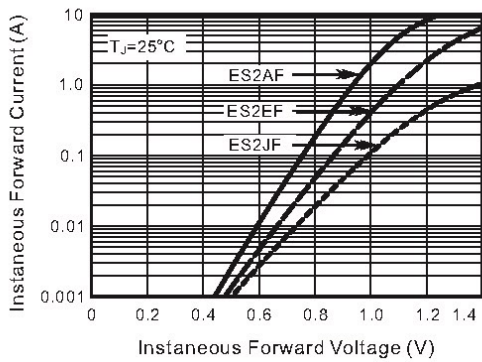
Maximum Average Forward Current Rating



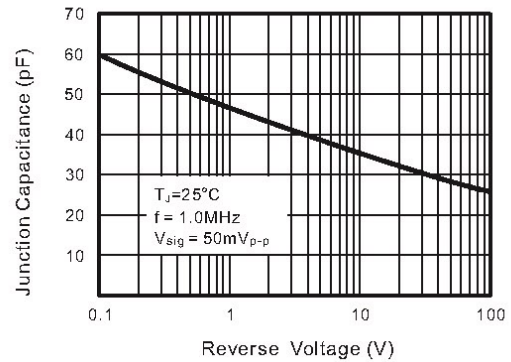
Typical Reverse Characteristics



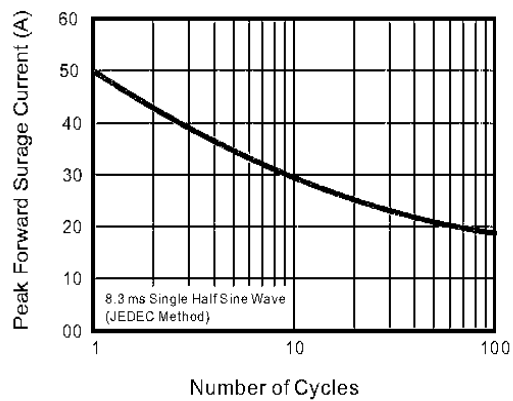
Typical Forward Characteristics



Typical Junction Capacitance



Maximum Non-Repetitive Peak Forward Surge Current



TOP DYNAMIC

